

In the Claims:

Please enter the following amended claims 18, 25, 26, and 32:

C¹
Sub D3

18. (Twice Amended) A process comprising:

- providing a semiconductor substrate;
- forming a gate oxide above the semiconductor substrate;
- forming a first polycrystalline silicon layer over the gate oxide;
- forming an interpoly dielectric;
- forming a second polycrystalline silicon layer over the interpoly dielectric;
- forming an anti-reflective coating above the second polycrystalline silicon layer;
- patterning the device to form a stack; and
- removing the anti-reflective coating without applying an oxide after the formation of the anti-reflective coating.

C²

25. (Once Amended) The process of claim 19, wherein the silicon oxynitride layer is removed before subjecting the silicon oxynitride layer to a temperature greater than about 400°C.

Sub D6

26. (Once Amended) A process comprising:

- providing a substrate;
- forming an anti-reflective coating above the substrate;

ENC 2
C²
patterning the substrate to form a stack; and
removing the anti-reflective coating without applying an oxide after the formation
of the anti-reflective coating.

C³
32. (Once Amended) The process of claim 26, wherein the silicon oxynitride layer
is removed before subjecting the silicon oxynitride layer to a temperature greater than
about 400°C.
